

# RLD-78MAT1 RLD-78PAT1

# AlGaAs double-hetero visible laser diodes

These were the world's first mass-produced laser diodes that were manufactured by molecular beam epitaxy and introduced with the RLD-78MA and RLD-78PA laser diodes. These diodes were especially developed for the higher ambient temperatures found in automobiles and have a higher reliability than the other CD laser diodes.

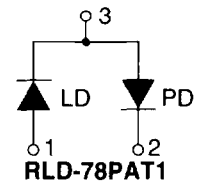
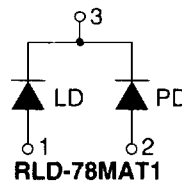
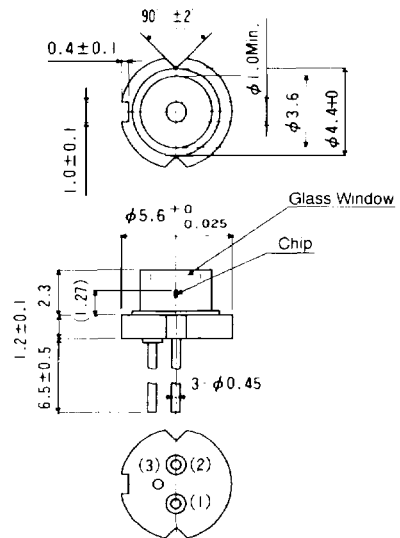
## Features

- noise is independent of feedback optical power
- specified signal-to-noise ratio is guaranteed over whole operating range
- reflected facet light is reduced
- one third the dispersion compared with conventional laser diodes
- very small, compact package; with close tolerances
- P type can be operated from single 5 V source

## Applications

- Automobile compact disc players

## Dimensions (Units : mm)



## Selection guide

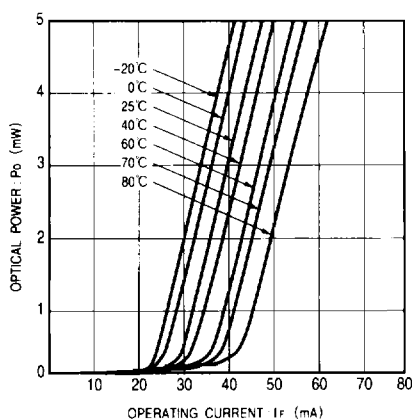
RLD-78MAT1	Standard
RLD-78PAT1	Semi-standard

## Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

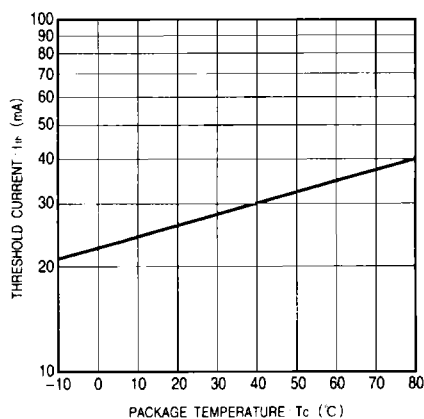
Parameter		Symbol	Limits	Unit
Optical power		$P_o$	5	mW
Reverse voltage	Laser	$V_R$	2	V
	PIN photodiode	$V_{R(PIN)}$	30	V
Operating temperature range		$T_{opr}$	-10 ~ +80	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-40 ~ +90	$^\circ\text{C}$

**Electro-optical characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Min	Typical	Max	Unit	Conditions
Threshold current	I <sub>th</sub>		35	60	mA	
Operating current	I <sub>op</sub>		45	70	mA	P <sub>o</sub> = 3 mW
Operating voltage	V <sub>op</sub>		1.9	2.3	V	P <sub>o</sub> = 3 mW
Differential efficiency	η	0.1	0.25	0.6	mW/mA	$\frac{2mW}{I_{P3mW} - I_{P1mW}}$
Monitor current	I <sub>m</sub>	0.1	0.2	0.6	mA	P <sub>o</sub> = 3 mW, V <sub>R(PIN)</sub> = 15 V
Beam divergence parallel	θ <sub>//</sub>	8	11	15	deg	P <sub>o</sub> = 3 mW
Beam divergence perpendicular	θ <sub>⊥</sub>	20	37	45	deg	
Beam tolerance parallel	Δφ <sub>//</sub>			±2	deg	
Beam tolerance perpendicular	Δφ <sub>⊥</sub>			±3	deg	
Emission point accuracy	ΔX ΔY ΔZ			±80	μm	
Wavelength	λ	770	785	810	nm	P <sub>o</sub> = 3 mW
Signal-to-noise ratio	S/N	60			dB	f = 720 kHz, Δf = 10 kHz



**Figure 1**



**Figure 2**

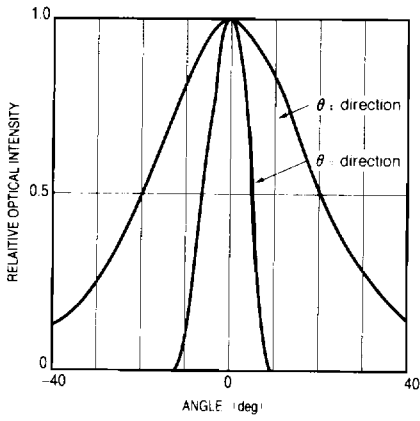


Figure 3

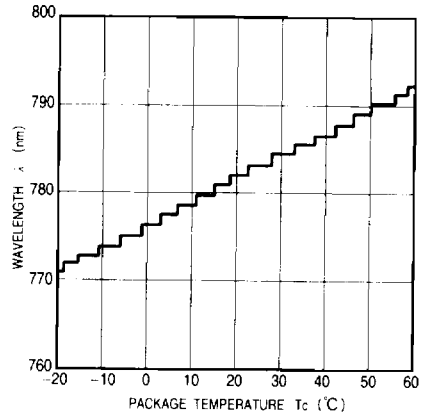


Figure 4

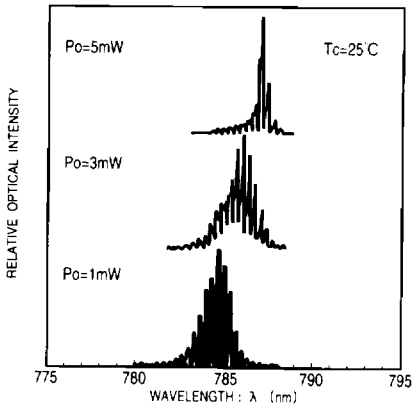


Figure 5

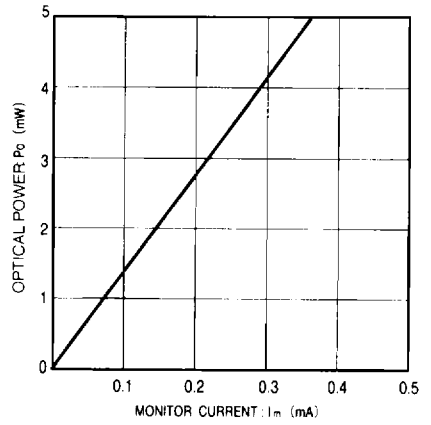


Figure 6

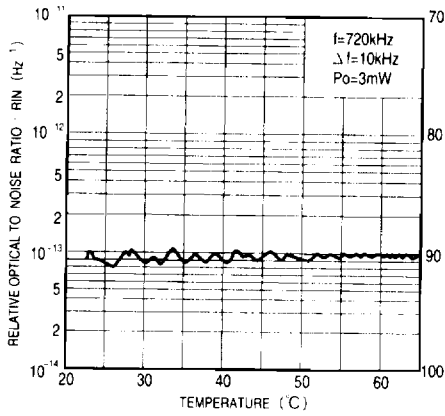


Figure 7

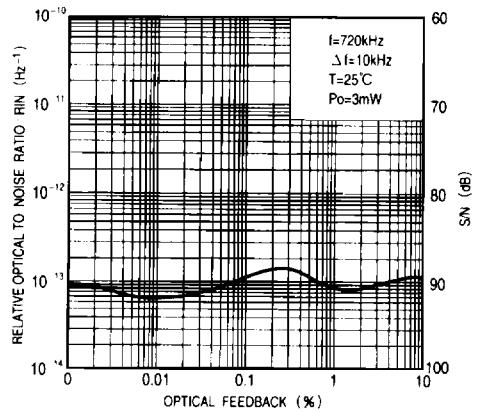


Figure 8